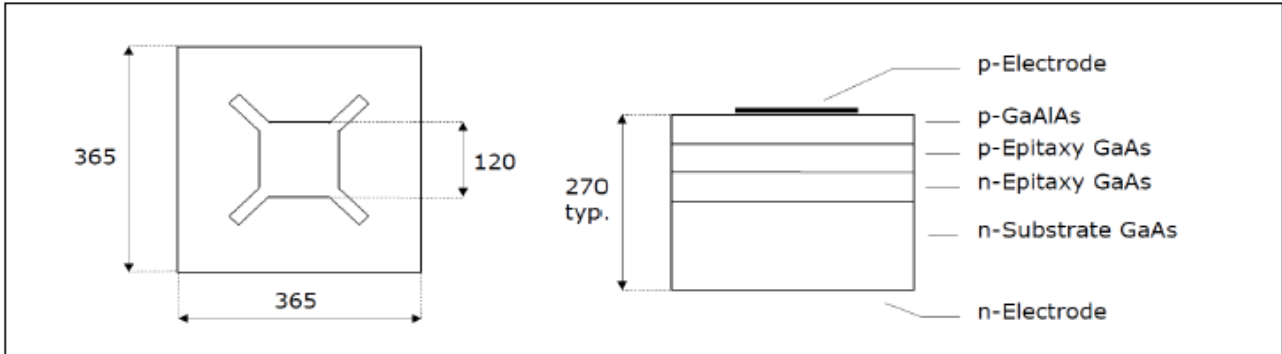




## ELC-935-17

Radiation	Type	Electrodes
Infrared	GaAs/GaAs, DH, with AlGaAs window	P (anode) up



### Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	$V_F$		1.2	1.4	V
Reverse current	$V_R = 5 \text{ V}$	$I_R$			100	$\mu\text{A}$
Radiant power*	$I_F = 20 \text{ mA}$	$\Phi_e$	1.5	2.5		mW
Peak wavelength	$I_F = 20 \text{ mA}$	$\lambda_p$	925	935	945	nm
FWHM	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		65		nm
Switching time	$I_F = 20 \text{ mA}$	$t_r, t_f$		500		ns

\*Measured on bare chip on TO-18 header

### Packing

Chips on adhesive film with wire-bond side top



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.